1.	Record Nr.	UNINA9910462785103321
	Titolo	Defects-recognition, imaging and physics in semiconductors XIV : selected, peer reviewed papers from the 14th International Conference on Defects-Recognition, Imaging and Physics in Semiconductors, September 25-29, 2011. Miyazaki, Japan / / edited by Hiroshi Yamada-Kaneta and Akira Sakai
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	Descrizione fisica	1 online resource (300 p.)
	Collana	Materials science forum ; ; vol. 725
	Altri autori (Persone)	Yamada-KanetaHiroshi SakaiAkira (Professor of engineering science)
	Disciplina	620.112972
	Soggetti	Semiconductors - Defects Physics Electronic books.
	Lingua di pubblicazione	Inglese
	Formato	Materiale a stampa
	Livello bibliografico	Monografia
	Note generali	Description based upon print version of record.
	Nota di contenuto	Defects-Recognition, Imaging and Physics in Semiconductors XIV; Preface, Message and Committee; Table of Contents; Chapter 1: Defects in SiC; Imaging and Strain Analysis of Threading-Edge and Basal-Plane Dislocations in 4H-SiC Using X-Ray Three-Dimensional Topography; Threading Dislocations in 4H-SiC Observed by Double-Crystal X-Ray Topography; Characterization of Dislocation Structures in Hexagonal SiC by Transmission Electron Microscopy; Photoluminescence Imaging and Wavelength Analysis of Basal Plane Frank-Type Defects in 4H-SiC Epilayers Formation of Nanovoids in Femtosecond Laser-Irradiated Single Crystals of Silicon CarbideElectron Beam Induced Current Observation of Dislocations in 4H-SiC Introduced by Mechanical Polishing; Basal Plane Dislocations in 4H-SiC Epilayers with Different Dopings; Frank Partial Dislocation in 4H-SiC Epitaxial Layer by MSE Method; Separation of the Driving Force and Radiation-Enhanced Dislocation Glide in 4H-SiC; Study of Defects Generated by Standard- and Plasma-Implantation

of Nitrogen Atoms in 4H-SiC Epitaxial Layers
Different Dissociation Behavior of [11-20] and Non-[11-20] Basal Plane Dislocations in 4H-Si under Electron Beam IrradiationDensity of Etch Pits on C-Face 4H-SiC Surface Produced by ClF3 Gas; Defect Related Leakage Current Components in SiC Schottky Barrier Diode; Rapid Terahertz Imaging of Carrier Density of 3C-SiC; Chapter 2: Nitride Materials and Devices; Cathodoluminescence Study of Ammonothermal GaN Crystals; The Effect of the Indenter Orientation on the Formation of Dislocations and Cracks in (0001) GaN Bulk Crystals; Defect Propagation from 3C-SiC to III-Nitride
Characterization of Dislocations in GaN Thin Film and GaN/AlN MultilayerMicroscopic Degradation Analysis of RF-Stressed AlGaN/GaN HEMTs; Chapter 3: III-V Compounds and Devices; Distribution of Misfit Dislocations at the InGaAs/GaAs(001) Interface Observed by Monochromatic X-Ray Topography; Effects of in Content on Anisotropies in Strain Relaxation Processes of InGaAs/GaAs (001) Measured by Real-Time Three-Dimensional Reciprocal Space Mapping; Nitrogen Related Deep Levels in GaAsN Films Investigated by a Temperature Dependence of Piezoelectric Photothermal Signal Intermixing in InP-Based Quantum Well Photonic Structures Induced by the Dry-Etching Process: A Spectral Imaging Cathodoluminescence StudyDefect Propagation in Broad-Area Diode Lasers; Kinetics of Defect Propagation during the Catastrophic Optical Damage (COD) in Broad-Area Diode Lasers; Nondestructive Measurement of Carrier Density in GaAs Using Relative Reflectivity of Two Terahertz Waves; Chapter 4: Photovoltaics: From Material to Module; Lock-In Thermography and Related Topics in Photovoltaic Research
EBIC Study on Metal Contamination at Intra Grain Defects in Multicrystalline Silicon for Solar Cells

Sommario/riassunto

This volume documents the latest understanding of many topics of current interest in the science and technology of defects in semiconductors. The investigation of defects in semiconductors is a little different to that in other fields of materials science: in order to observe defects in semiconductors and elucidate their physical nature, a very wide range of tools and techniques has been introduced or created; thanks to the inventive ideas of the researchers. This work clearly reflects the lively state of defect investigation in semiconductors. Review from Book News Inc.: Drawn from papers del

2. Record Nr. UNISALENTO991002416899707536

Autore	Hansotte, Georges
Titolo	Inventaire des archives du charbonnage des Six-Bonniers à Seraing / par Georges Hansotte
Pubbl/distr/stampa	Bruxelles : [s.n.], 1959
Descrizione fisica	19 p. ; 26 cm
Altri autori (Enti)	Archives de l'État <Liegi>
Disciplina	338.272
Soggetti	Carbone - Belgio - Storia - Fonti
Lingua di pubblicazione	Francese
Formato	Materiale a stampa
Livello bibliografico	Monografia

3. Record Nr. UNINA9910917172003321

Autore	Jorm Anthony
Titolo	Expert Consensus in Science / / by Anthony Jorm
Pubbl/distr/stampa	Singapore : , : Springer Nature Singapore : , : Imprint : Palgrave Macmillan, , 2025
ISBN	9789819792221 9819792223
Edizione	[1st ed. 2025.]
Descrizione fisica	1 online resource (241 pages)
Disciplina	501.9
Soggetti	Science - Social aspects Expertise Science - Philosophy Science in popular culture Communication in science Science and Technology Studies Expertise Studies Sociology of Science Philosophy of Science Public Understanding of Science Science Communication

Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di contenuto	Chapter 1: The Controversy over Expert Consensus in Science -- Chapter 2: Consensus Pervades Scientific Processes -- Chapter 3: Expert Consensus to Establish Scientific Truths -- Chapter 4: Spontaneous and Deliberative Processes to Reach Consensus -- Chapter 5: Expert Consensus to Guide Practice and Policy -- Chapter 6: Expert Consensus on Research Methods -- Chapter 7: Specifying “Experts” and “Consensus” -- Chapter 8: Methods for Determining Deliberative Consensus -- Chapter 9: How Wisdom-of-Crowds Research Can Help Improve Deliberative Consensus Methods -- Chapter 10: Towards a “Wisdom of Scientific Crowds” -- Chapter 11: Using Expert Consensus to Persuade the Public.
Sommario/riassunto	This Open Access book shows how expert consensus pervades all areas of science. It explores, in particular, the role of consensus in establishing scientific truth, in guiding professional practice and policy and agreeing on what are acceptable scientific methodologies. For some scientific issues, a consensus forms spontaneously among scientists working on a topic, while for others, where the issues are complex, a formal deliberative consensus process is commonly needed. Deliberative consensus processes are becoming more important as scientists increasingly deal with complex multi-disciplinary issues of policy importance such as climate change due to human activity. While deliberative consensus processes are commonly used, they often lead to criticism from consensus skeptics. The book argues that deliberative consensus processes in science can be improved and proposes a number of realistic ways forward, ending with a discussion of whether communicating the scientific consensus on a topic is a good way to persuade the public. Anthony Jorm is an Emeritus Professor at the University of Melbourne and National Health & Medical Research Council Leadership Fellow. His research focuses on building the community’s capacity for prevention and early intervention with mental disorders. He has particular methodological expertise in the use of the Delphi consensus method in health research. He is Editor-in-Chief of the journal Mental Health & Prevention. He is the co-founder and Director of the not-for-profit organization Mental Health First Aid International.